

APPENDIX

Changes to Claims:

Claims 15 and 16 are added.

The following are marked-up versions of the amended claims:

1. (Amended) A semiconductor device, comprising:

~~_____ a silicon substrate and~~

a metal-oxide-semiconductor field-effect transistor ~~formed on said silicon~~
~~substrate,~~

~~_____ wherein a gate electrode of said transistor comprises a germanium film that~~
includes:

_____ a gate insulation film and a gate electrode on the gate insulation film,
the gate electrode including a germanium film on the gate insulation film.

7. (Amended) A semiconductor device, comprising:

an n-channel metal-oxide-semiconductor field-effect transistor; and

a p-channel metal-oxide-semiconductor field-effect transistor,

~~wherein a gate electrode of each of said transistors comprises any one of a~~
~~single-crystalline germanium film, a polycrystalline germanium film or an amorphous~~
~~germanium film in which p-type impurities are doped~~at least one of the n-channel metal-
oxide-semiconductor field-effect transistor and the p-channel metal-oxide-semiconductor
field-effect transistor including:

_____ a gate insulation film and a gate electrode on the gate insulation film,
the gate electrode including a germanium film on the gate insulation film.